

General Description

Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

Features

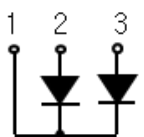
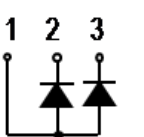
- Repetitive Reverse Voltage : $V_{RRM}=1200V$
- Low Forward Voltage : $V_F(\text{typ.}) = 2.2V$
- Average Forward Current : $I_F(\text{Av.})=100A @T_C=100^\circ C$
- Ultra-Fast Reverse Recovery Time : $t_{rr}(\text{typ.}) = 40ns$
- Extensive Characterization of Recovery Parameters
- Reduced EMI and RFI
- Isolation Type Package

Applications

- High Speed & High Power converters, Welders
- Various Switching and Telecommunication Power Supply



Ordering Information

Product Name	MPKB2SA100U120	MPKB2SB100U120
Optional Information	Side Common & N-type 	Side Common & P-type 

Absolute Maximum Ratings @Tc = 25°C (Per Leg)

Characteristics	Conditions	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Reverse DC Voltage		$V_{R(DC)}$	960	V
Average Forward Current	$T_C=25^\circ C$	$I_{F(AV)}$	200	A
	$T_C=100^\circ C$		100	A
Surge(non-repetitive) Forward Current	One Half Cycle at 60Hz, Peak Value	I_{FSM}	1400	A
I^2t for Fusing	Value for One Cycle Current, $t_w = 8.3ms, T_j = 25^\circ C$ Start	I^2t	8.13×10^3	A^2s
Junction Temperature		T_J	-40 ~ 150	$^\circ C$
Maximum Power Dissipation		P_D	290	W
Isolation Voltage	@AC 1 minutes	V_{isol}	2500	V
Storage Temperature		T_{stg}	-40 ~ 125	$^\circ C$
Mounting Torque(M6)		-	4.0	N.m
Terminal Torque(M5)	Typical Including Screws	-	2.0	N.m
Weight		-	120	g

Electrical Characteristics @T_c = 25°C(unless otherwise specified)

Characteristics	Conditions	Symbol	Min.	Typ.	Max.	Unit	
Cathode Anode Breakdown Voltage	I _R =100uA	V _R	1200	-	-	V	
Diode Maximum Forward Voltage	I _F =100A	V _{FM}	T _c =25°C	-	2.2	2.8	V
			T _c =100°C	-	2.0	-	
Diode Peak Reverse Recovery Current	T _c =100°C, V _R applied	I _R RM	-	-	1.0	mA	
Diode Reverse Recovery Time	I _F =1A, V _R =30V di/dt = -200A/uS	t _{rr}	-	40	60	ns	
Diode Reverse Recovery Time	I _F =100A, V _R =600V di/dt = -200A/uS	t _{rr}	T _c =25°C	-	110	-	ns
			T _c =100°C	-	180	-	

Thermal Characteristics

Characteristics	Conditions	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance(Isolation Type)	Junction to Case	R _{th(j-c)}	-	-	0.42	°C/W

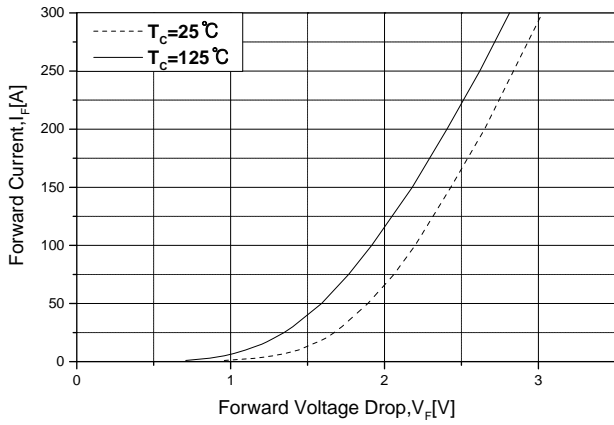


Fig.1 Typical Forward Voltage Drop vs. Instantaneous Forward Current

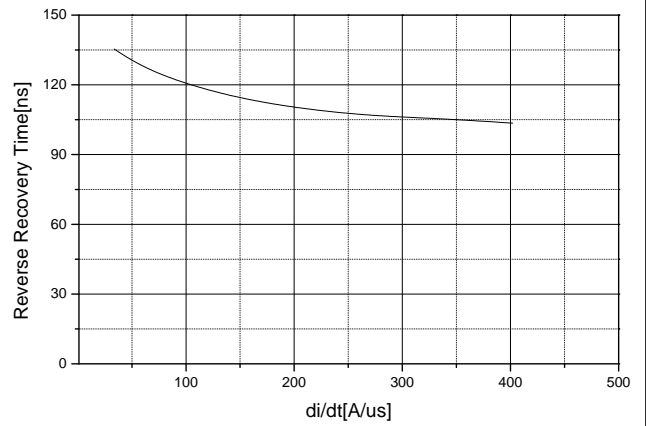


Fig.2 Typical Reverse Recovery Time Vs. $-di/dt$

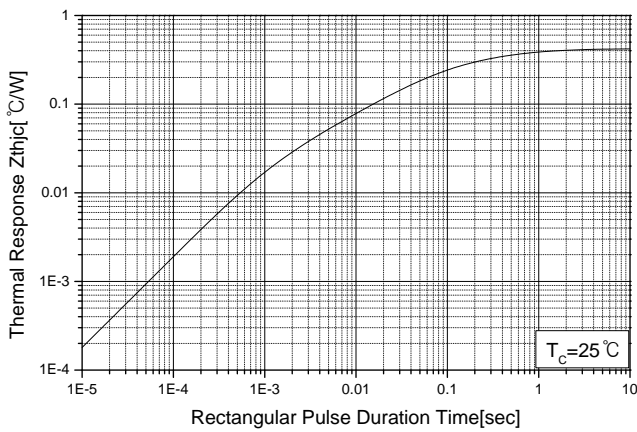


Fig.3 Transient Thermal Impedance (Z_{thjc}) Characteristics

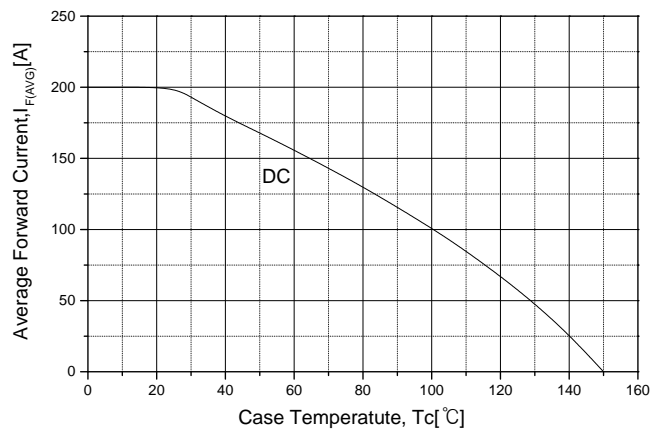
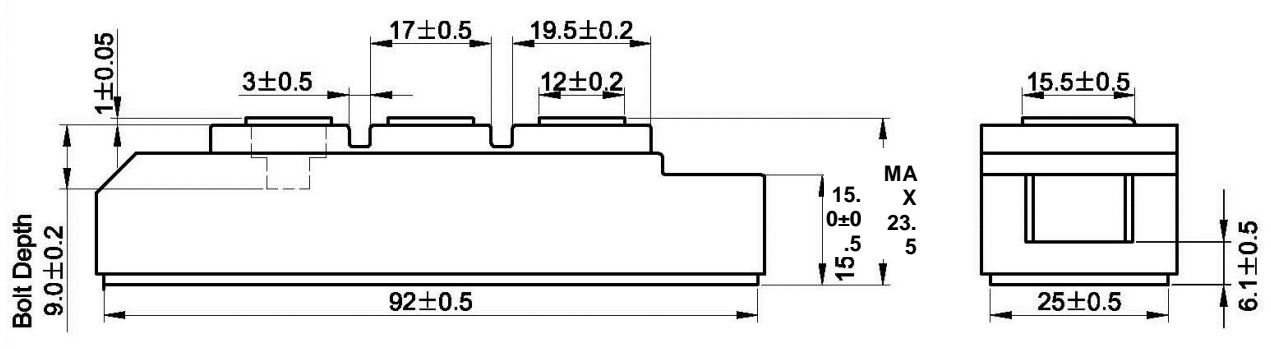
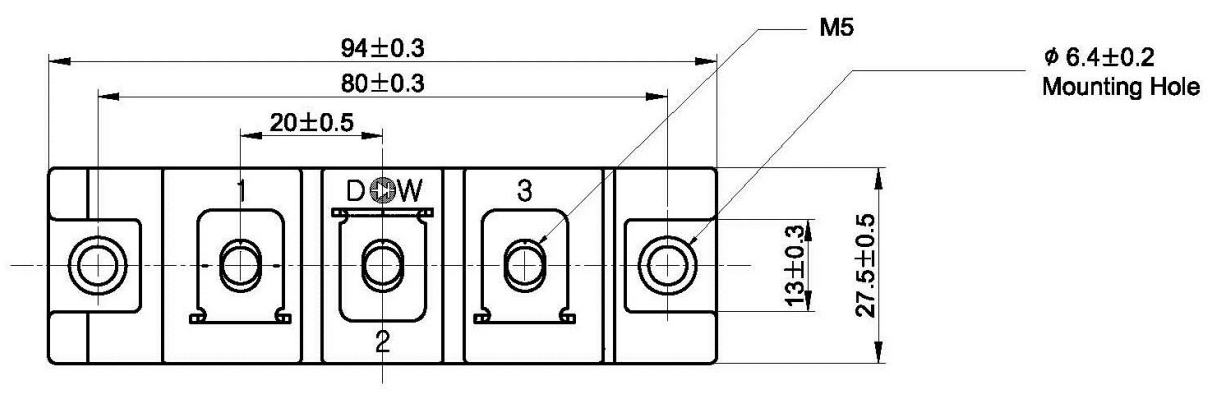


Fig.4 Forward Current Derating Curve

Package Dimension

5DM-1

Dimensions are in millimeters, unless otherwise specified



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